Ordering number : ENA1077A

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

NPN Epitaxial Planar Silicon Transistor

2SC5231A — VHF to UHF Wide-Band Low-Noise Amplifier Applications

Features

- Low-noise : NF=1.0dB typ (f=1GHz)
- High gain : $|S21e|^2$=12dB typ (f=1GHz)
- High cut-off frequency : f_T=7GHz typ
- Ultrasmall-sized package permitting applied sets to be made small and slim

Specifications

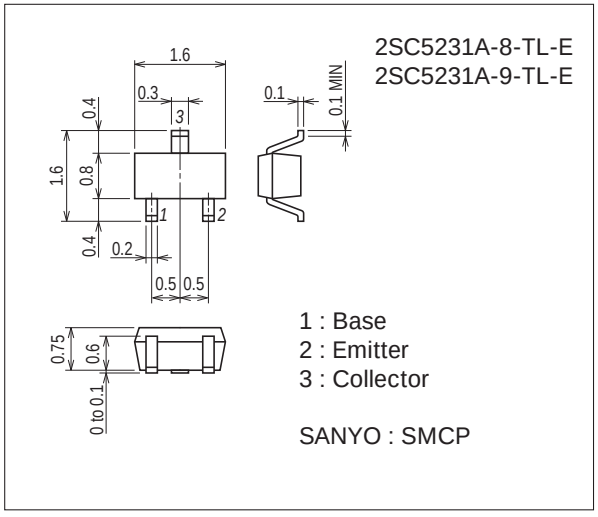
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		20	V
Collector-to-Emitter Voltage	V_{CEO}		10	V
Emitter-to-Base Voltage	V_{EBO}		2	V
Collector Current	I_C		70	mA
Collector Dissipation	P_C		100	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Package Dimensions

unit : mm (typ)

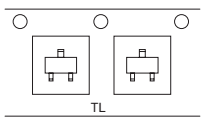
7027A-002



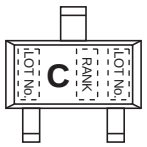
Product & Package Information

- Package : SMCP
- JEITA, JEDEC : SC-75, SOT-416
- Minimum Packing Quantity : 3,000 pcs./reel

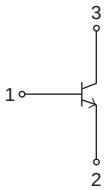
Packing Type: TL



Marking



Electrical Connection



Electrical Characteristics at Ta=25°C

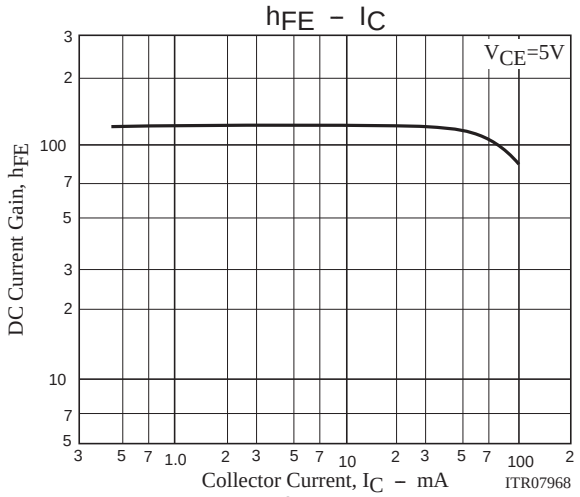
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=10V, I_E=0A			1.0	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=1V, I_C=0A			10	μA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=20mA	60*		270*	
Gain-Bandwidth Product	f_T	V_{CE}=5V, I_C=20mA	5	7		GHz
Output Capacitance	Cob	V_{CB}=10V, f=1MHz		0.7	1.2	pF
Reverse Transfer Capacitance	Cre			0.45		pF
Forward Transfer Gain	$|S21e|^2$1	V_{CE}=5V, I_C=20mA, f=1GHz	9	12		dB
	$|S21e|^2$2	V_{CE}=2V, I_C=3mA, f=1GHz		8.5		dB
Noise Figure	NF	V_{CE}=5V, I_C=7mA, f=1GHz		1.0	1.8	dB

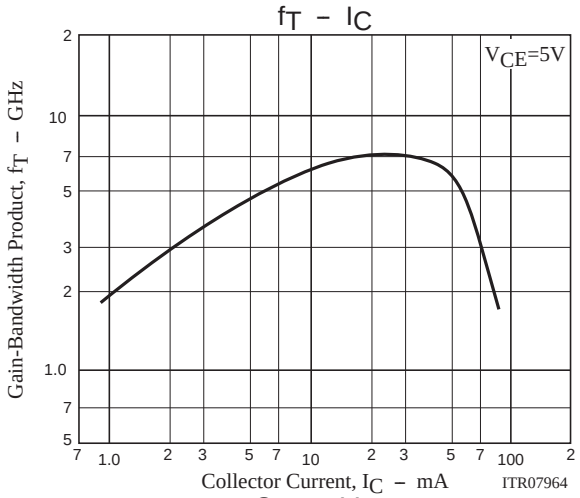
* : The 2SC5231A is classified by 20mA h_{FE} as follows :

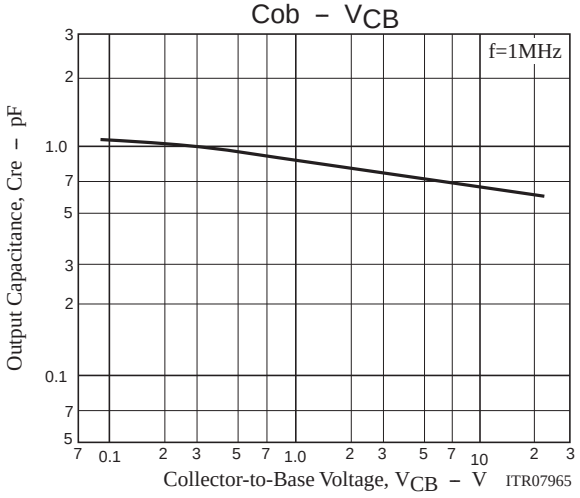
Rank	7	8	9
h_{FE}	60 to 120	90 to 180	135 to 270

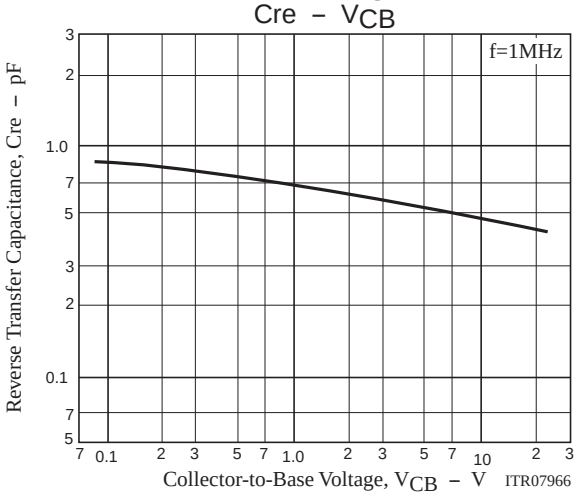
Ordering Information

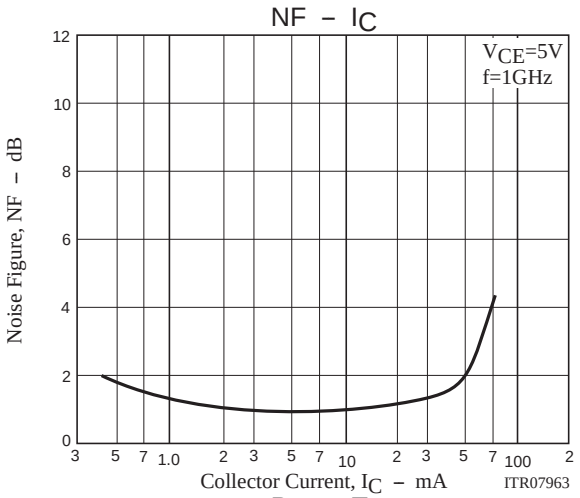
Device	Package	Shipping	memo
2SC5231A-8-TL-E	SMCP	3,000pcs./reel	Pb Free
2SC5231A-9-TL-E	SMCP	3,000pcs./reel	

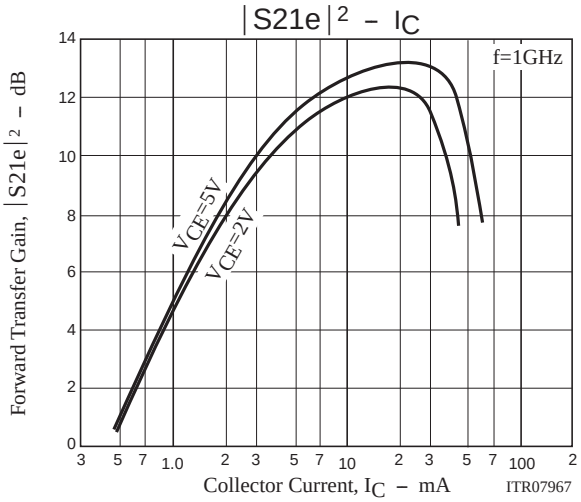


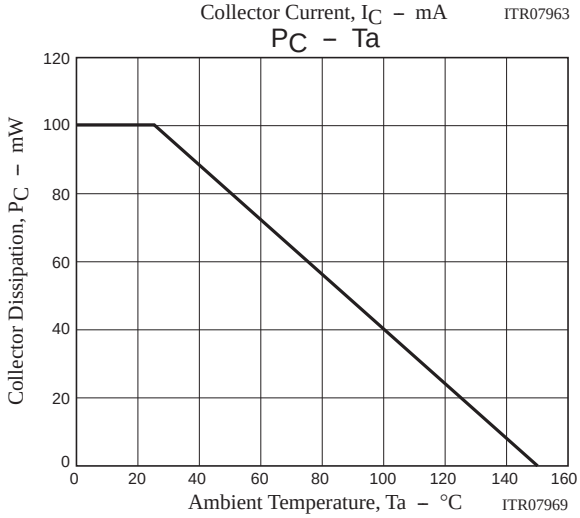




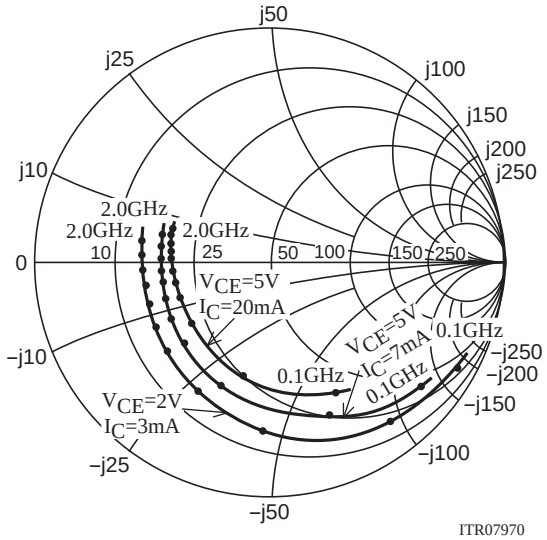



NF – IC
VCE=5V
f=1GHz
Noise Figure, NF – dB
Collector Current, IC – mA
ITR07963

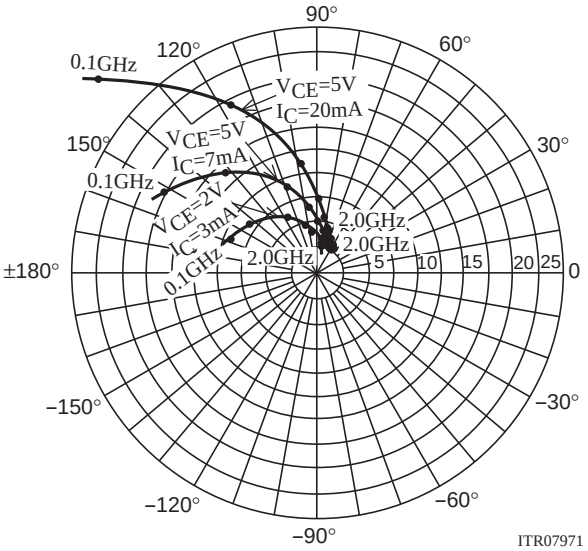

|S21e|2 – IC
f=1GHz
VCE=5V
VCE=2V
Forward Transfer Gain, |S21e|2 – dB
Collector Current, IC – mA
ITR07967


PC – Ta
Collector Dissipation, PC – mW
Ambient Temperature, Ta – °C
ITR07969

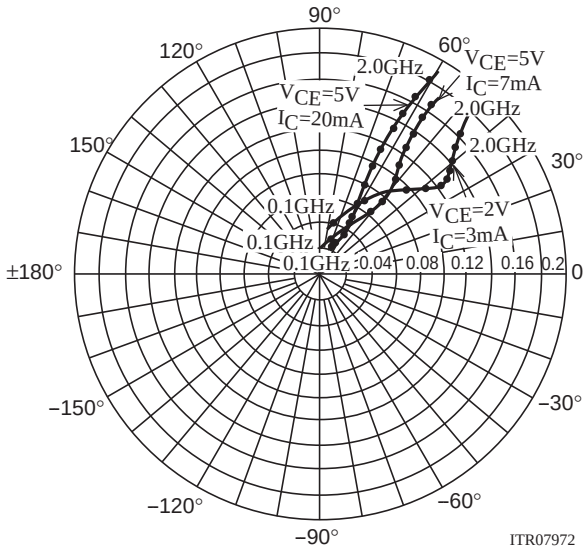
S11e
f=100MHz, f=200MHz to 2000MHz(200MHz Step)



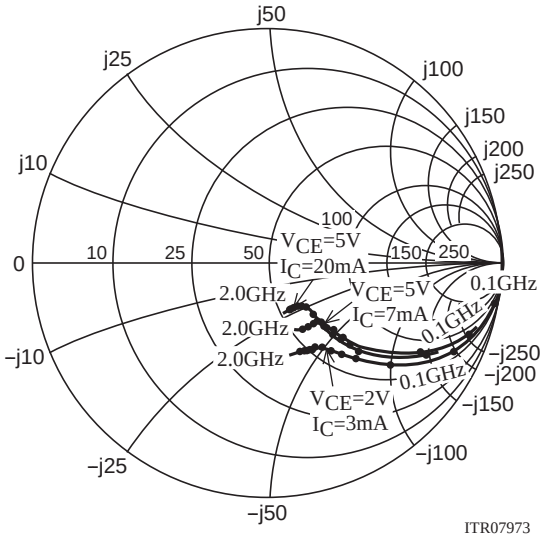
S21e
f=100MHz, f=200MHz to 2000MHz(200MHz Step)



S12e
f=100MHz, f=200MHz to 2000MHz(200MHz Step)



S22e
f=100MHz, f=200MHz to 2000MHz(200MHz Step)



S Parameters (Common emitter)

V_{CE}=5V, I_C=7mA, Z_O=50Ω

Freq(MHz)	|S11|	∠S11	|S21|	∠S21	|S12|	∠S12	|S22|	∠S22
100	0.786	-40.7	17.507	151.3	0.028	70.1	0.898	-20.4
200	0.677	-72.4	13.998	131.4	0.046	58.0	0.739	-33.4
400	0.546	-112.7	9.061	108.6	0.064	49.6	0.525	-43.7
600	0.492	-135.2	6.442	96.1	0.076	49.3	0.423	-46.7
800	0.473	-150.0	5.005	87.3	0.087	50.8	0.374	-44.4
1000	0.465	-160.0	4.073	80.4	0.099	52.6	0.346	-49.7
1200	0.457	-169.5	3.449	74.0	0.111	54.0	0.332	-51.6
1400	0.451	-176.2	2.989	68.6	0.124	55.2	0.321	-54.1
1600	0.449	177.8	2.658	63.8	0.138	56.6	0.319	-56.2
1800	0.454	172.5	2.378	58.4	0.151	56.7	0.313	-60.0
2000	0.460	167.1	2.154	54.0	0.166	56.7	0.311	-63.2

V_{CE}=5V, I_C=20mA, Z_O=50Ω

Freq(MHz)	|S11|	∠S11	|S21|	∠S21	|S12|	∠S12	|S22|	∠S22
100	0.601	-65.8	28.967	137.1	0.023	64.1	0.757	-32.9
200	0.497	-103.7	19.309	116.6	0.035	57.0	0.534	-50.3
400	0.435	-139.6	10.891	98.6	0.050	58.7	0.345	-50.3
600	0.419	-156.6	7.461	89.3	0.065	61.3	0.280	-50.7
800	0.414	-166.6	5.695	82.5	0.081	63.1	0.251	-51.3
1000	0.413	-174.0	4.613	77.0	0.098	63.8	0.235	-52.9
1200	0.413	178.6	3.870	71.8	0.114	63.9	0.226	-55.1
1400	0.411	173.8	3.345	66.9	0.131	63.6	0.221	-57.7
1600	0.413	169.6	2.960	62.7	0.148	63.2	0.220	-60.2
1800	0.416	165.1	2.655	58.0	0.165	61.8	0.219	-64.8
2000	0.422	160.3	2.406	54.0	0.182	60.6	0.218	-68.3

V_{CE}=2V, I_C=3mA, Z_O=50Ω

Freq(MHz)	|S11|	∠S11	|S21|	∠S21	|S12|	∠S12	|S22|	∠S22
100	0.888	-30.2	9.280	158.6	0.038	73.6	0.949	-15.1
200	0.815	-56.4	8.218	141.3	0.067	60.5	0.849	-26.9
400	0.690	-96.0	6.074	116.7	0.098	45.1	0.657	-41.1
600	0.616	-120.7	4.517	101.4	0.112	38.4	0.539	-47.6
800	0.584	-138.0	3.610	90.4	0.120	35.8	0.475	-51.2
1000	0.566	-150.7	2.995	81.9	0.125	35.7	0.434	-54.5
1200	0.555	-161.2	2.540	74.2	0.131	36.5	0.410	-57.5
1400	0.546	-169.3	2.213	67.5	0.137	38.4	0.393	-60.7
1600	0.541	-176.4	1.982	62.0	0.143	40.7	0.391	-64.0
1800	0.545	177.1	1.774	55.9	0.152	42.5	0.382	-67.8
2000	0.547	170.9	1.614	50.9	0.163	44.7	0.381	-72.1

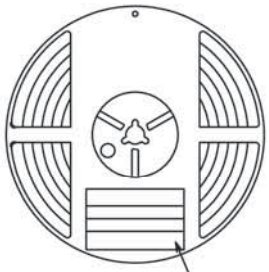
Embossed Taping Specification

2SC5231A-8-TL-E, 2SC5231A-9-TL-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
SMCP	SMCP	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

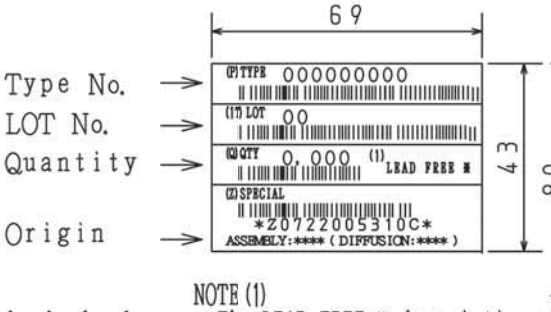
Packing method



Reel label

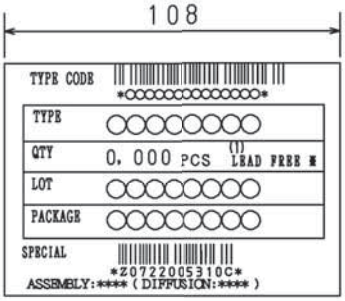
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.

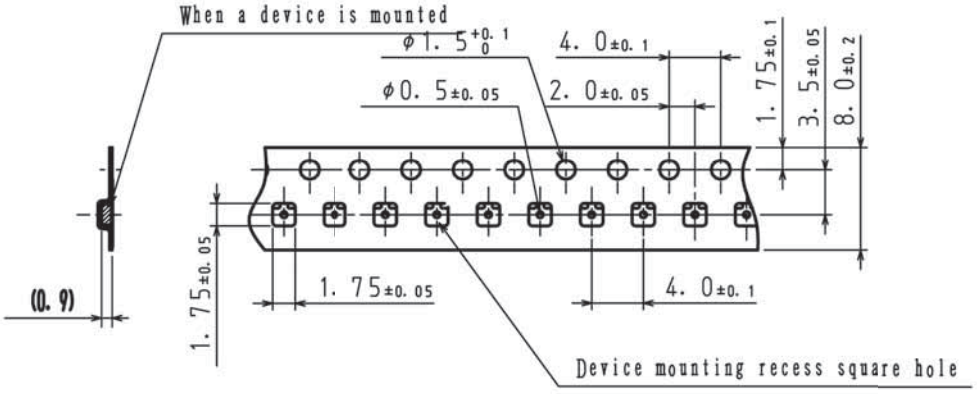


NOTE (1)
The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

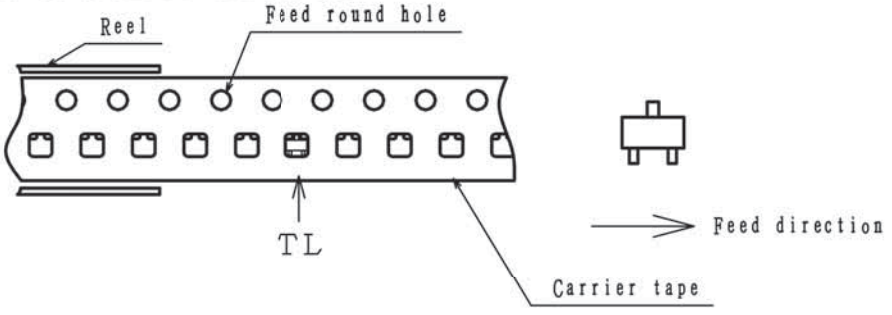
Label	JEITA Phase
••••••••••	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



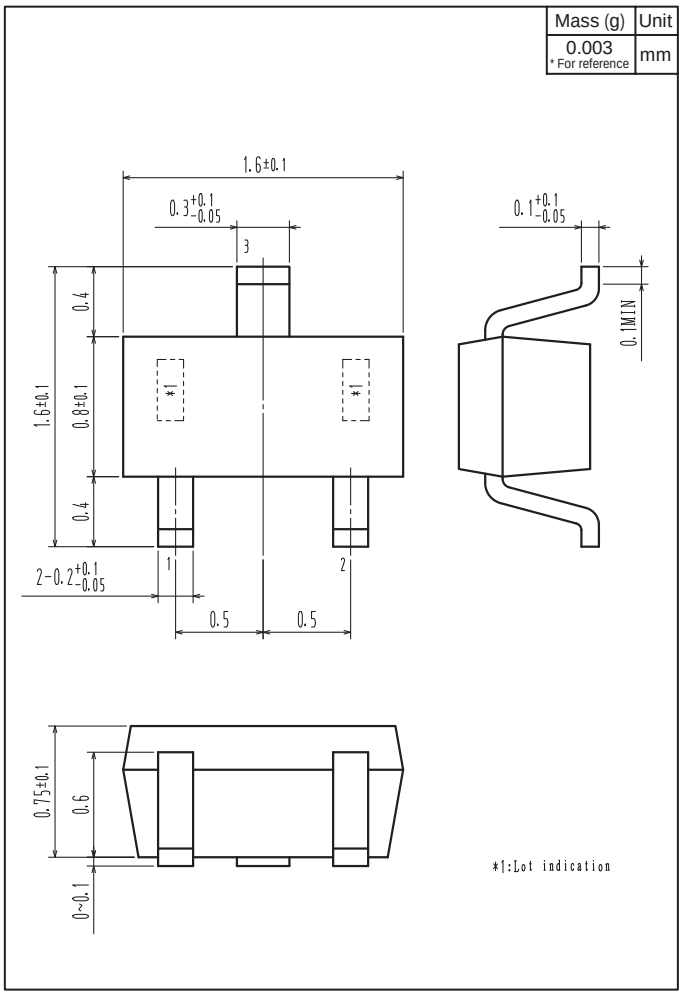
2-2. Device placement direction



Those with one electrode terminal on the feed hole side·····TL

Outline Drawing

2SC5231A-8-TL-E, 2SC5231A-9-TL-E



Land Pattern Example